

ABC856AW-HF Thru. ABC858CW-HF (PNP)

RoHS Device

Halogen Free



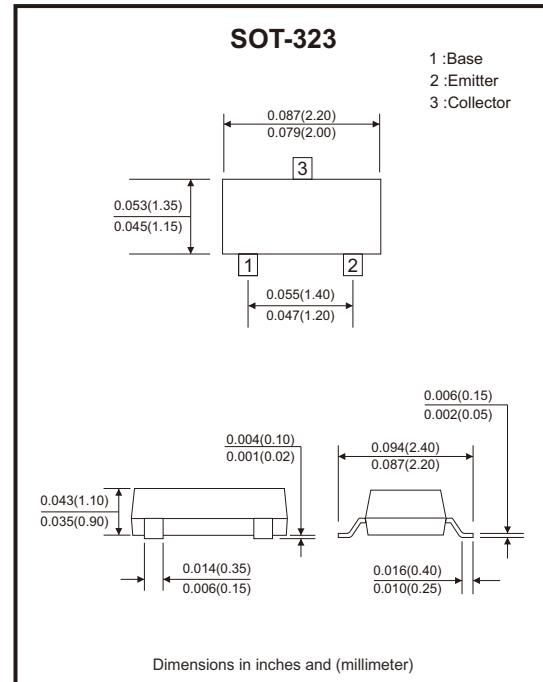
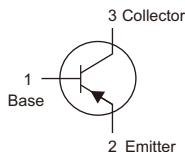
Features

- For AF input stages and driver applications.
- High current gain.
- Low collector-emitter saturation voltage.
- Low noise between 30Hz and 15kHz.
- AEC-Q101 Qualified.

Mechanical data

- Case: SOT-323, molded plastic.

Circuit Diagram



Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-base voltage ABC856W-HF ABC857W-HF ABC858W-HF	V _{CBO}	-80	V
		-50	
		-30	
Collector-emitter voltage ABC856W-HF ABC857W-HF ABC858W-HF	V _{CEO}	-65	V
		-45	
		-30	
Emitter-base voltage	V _{EBO}	-5	V
Collector current-continuous	I _C	-100	mA
Peak collector current	I _{CM}	-200	mA
Peak base current	I _{BM}	-200	mA
Collector dissipation	P _C	200	mW
Junction and storage temperature range	T _J , T _{STG}	-65 to +150	°C

General Purpose Transistor

Electrical Characteristics (Ta= 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage ABC856W-HF ABC857W-HF ABC858W-HF	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-80			V
			-50			
			-30			
Collector-emitter breakdown voltage ABC856W-HF ABC857W-HF ABC858W-HF	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-65			V
			-45			
			-30			
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-15	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain ABC856AW, 857AW, 858AW ABC856BW, 857BW, 858BW ABC857CW, 858CW	h_{FE}	$V_{CE} = -5V, I_C = -10\mu A$	140			
			250			
			480			
DC current gain ABC856AW, 857AW, 858AW ABC856BW, 857BW, 858BW ABC857CW, 858CW	h_{FE}	$V_{CE} = -5V, I_C = -2mA$	125	180	250	
			220	290	475	
			420	520	800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -0.5mA$		-0.075	-0.3	V
		$I_C = -100mA, I_B = -5mA$		-0.25	-0.65	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -0.5mA$		-0.7		V
		$I_C = -100mA, I_B = -5mA$		-0.85		
Base-emitter voltage	$V_{BE(on)}$	$I_C = -2mA, V_{CE} = 5V$	-0.6		-0.75	V
		$I_C = -10mA, V_{CE} = 5V$	-		-0.82	
Transition frequency	f_T	$V_{CE} = -5V, I_C = -20mA, f = 100MHz$		250		MHz
Collector-base capacitance	C_{cb}	$V_{CB} = -10V, f = 1MHz$		3	5	pF
Emitter-base capacitance	C_{eb}	$V_{EB} = -0.5V, f = 1MHz$		10	15	pF

Rating and Characteristic Curves (ABC856AW-HF Thru. ABC858CW-HF)

Fig.1 - Total Power Dissipation

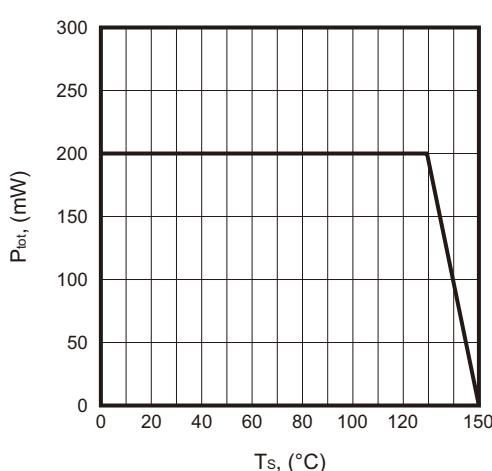
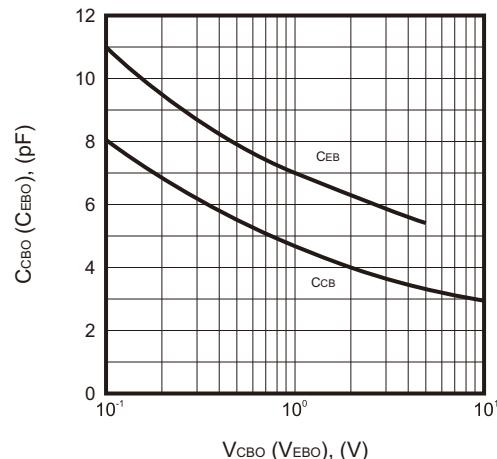


Fig.2 - Collector-Base Capacitance
Emitter-Base Capacitance



Company reserves the right to improve product design , functions and reliability without notice.

REV:A

General Purpose Transistor

Comchip
SMD Diode Specialist

Rating and Characteristic Curves (ABC856AW-HF Thru. ABC858CW-HF)

Fig.3 - Transition Frequency

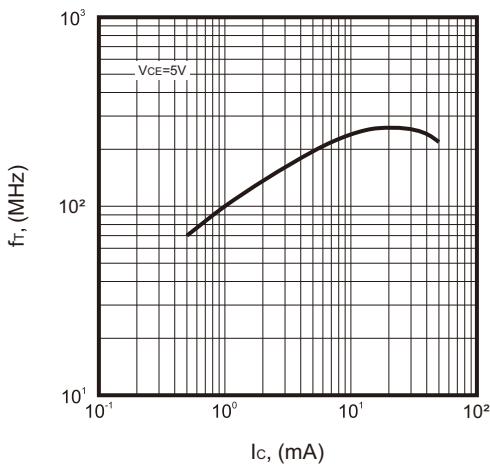


Fig.4 - Collector Cutoff Current

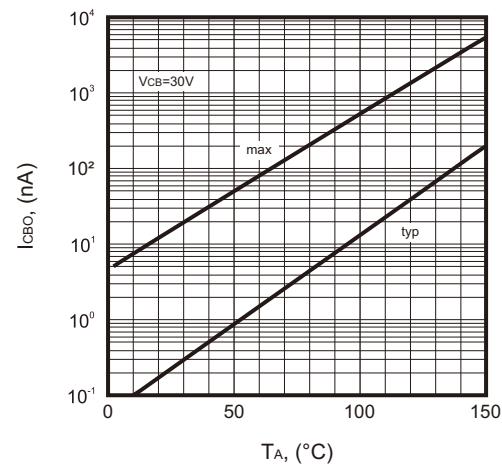


Fig.5 - Collector-Emitter Saturation Voltage

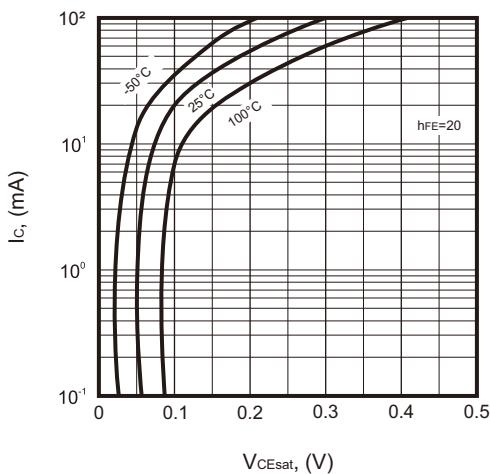


Fig.6 - DC Current Gain

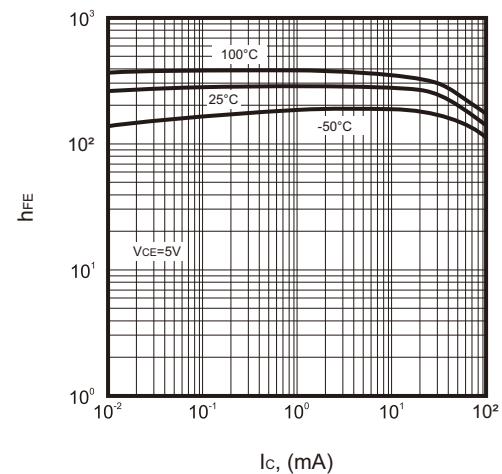
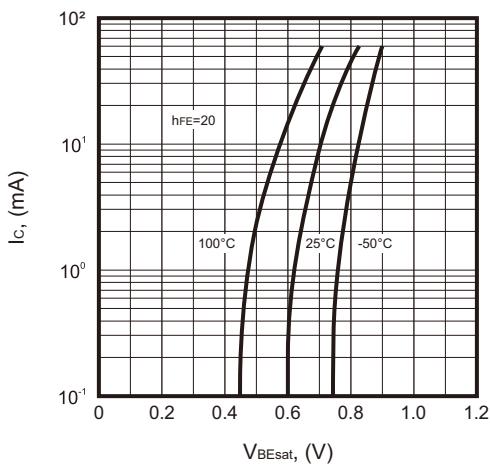


Fig.7 - Base-Emitter Saturation Voltage

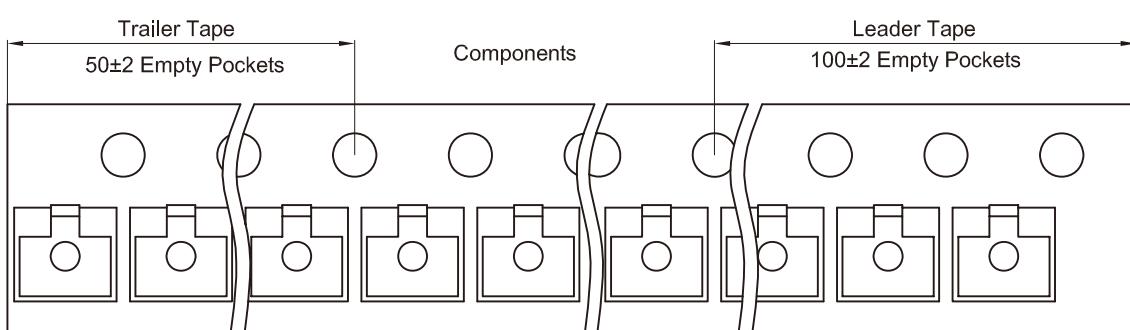
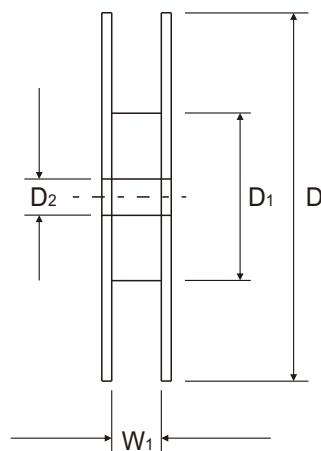
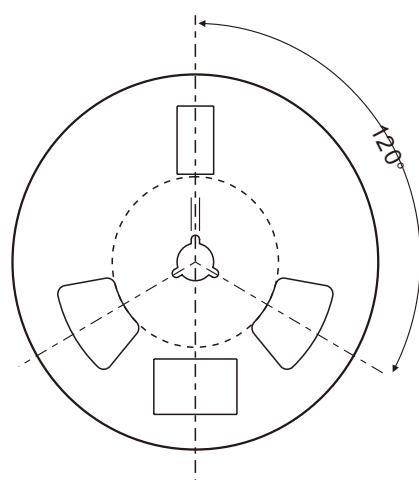
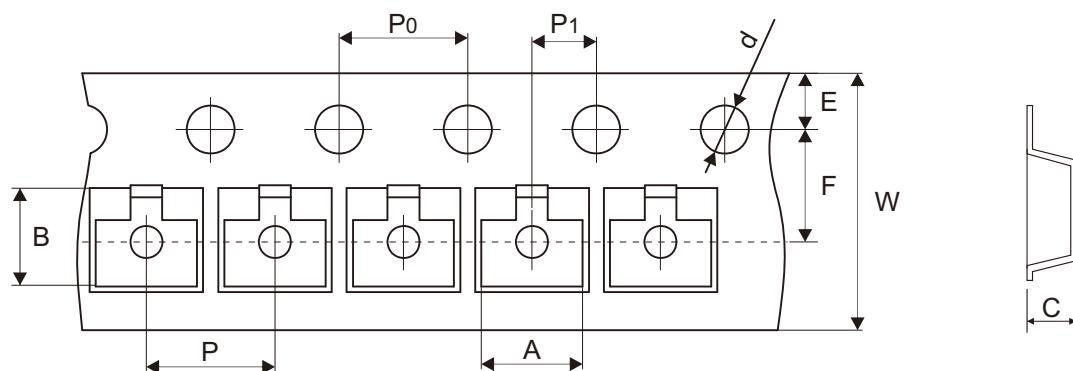


Company reserves the right to improve product design , functions and reliability without notice.

General Purpose Transistor

Comchip
SMD Diode Specialist

Reel Taping Specification



	SYMBOL	A	B	C	d	D	D1	D2
SOT-323	(mm)	2.25 ± 0.10	2.55 ± 0.10	1.20 ± 0.10	1.50 ± 0.10	178.00 ± 1.00	54.00 ± 0.50	13.00 ± 0.50
	(inch)	0.089 ± 0.004	0.100 ± 0.004	0.047 ± 0.004	0.059 ± 0.004	7.008 ± 0.039	2.126 ± 0.020	0.512 ± 0.020

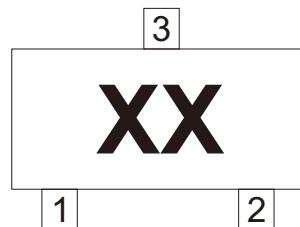
	SYMBOL	E	F	P	P0	P1	W	W1
SOT-323	(mm)	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	8.00 ± 0.30 -0.10	9.50 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.002	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.315 ± 0.012 -0.004	0.374 ± 0.039

Company reserves the right to improve product design , functions and reliability without notice.

REV:A

Marking Code

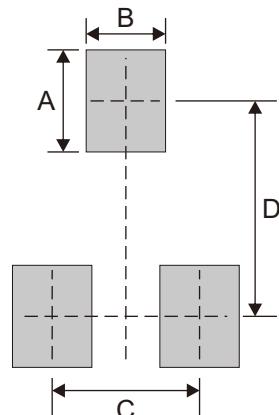
Part Number	Marking Code
ABC856AW-HF	3A
ABC857AW-HF	3E
ABC858AW-HF	3J
ABC856BW-HF	3B
ABC857BW-HF	3F
ABC858BW-HF	3K
ABC857CW-HF	3G
ABC858CW-HF	3L



xx = Product type marking code

Suggested P.C.B. PAD Layout

SIZE	SOT-323	
	(mm)	(inch)
A	0.90	0.035
B	0.70	0.028
C	1.30	0.051
D	1.90	0.075



Note: 1.The pad layout is for reference purposes only.

Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-323	3,000	7

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Comchip manufacturer:

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NTE158](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE63](#) [C4460](#)
[2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SD2150T100R](#) [SP000011176](#) [FMMTA92QTA](#) [2N2369ADCSM](#)
[2N5769](#) [2SC2412KT146S](#) [2SC5490A-TL-H](#) [2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)
[US6T6TR](#) [NJL0281DG](#) [732314D](#) [CMXT3906 TR](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#)
[NJL0302DG](#) [2N3583](#) [2SA1434-TB-E](#) [2SC3143-4-TB-E](#) [2SD1621S-TD-E](#) [NTE103](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE101](#) [NTE13](#)
[NTE15](#) [NTE16001](#)